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PATENT
Customer No. 22,852
Attorney Docket No. 2887.0258

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	
)	
Toshiyuki Sasaki et al.)	Group Art Unit: 2812
)	
Serial No.: 10/688,965)	
)	Examiner: Geyer, Scott B.
Filed: October 21, 2003)	
)	
For: METHOD OF MANUFACTURING)	Confirmation No.: 7425
A SEMICONDUCTOR DEVICE)	
INCLUDING A DIELECTRIC FILM)	
FORMED BETWEEN FIRST AND)	
SECOND ELECTRODE LAYERS)	
(as amended))	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

REPLY TO OFFICE ACTION

In reply to the Office Action mailed February 10, 2006, the period for response to which extends through May 10, 2006, please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims in this paper.

Remarks/Arguments follow the amendment sections of this paper.

Attachments include:

- 1) Article titled "Physical and Electrical Properties of Ta-N, Mo-N, and W-N Electrodes of HfO₂ High-k Gate Dielectric"; and
- 2) http://www.reade.com/Products/Nitrides/tungsten_nitride.html.